

**SPECIFICATION OF LED CHIP**  
**C615-35V**  
**[ ORANGE ]**

1) Commodity Type and Physical Characteristics.

- |                      |                              |                   |
|----------------------|------------------------------|-------------------|
| 1. Material          | InGaAlP/GaAs                 |                   |
| 2. Electrode         | Top Side P (anode) side      | : Au Alloy/Al Pad |
|                      | Bottom Side N (cathode) side | : Au Alloy        |
| 3. Electrode Pattern |                              | Fig.1             |
| 4. Chip Size         |                              | Fig.2             |
| 5. Chip Thickness    |                              | Fig.2             |
| 6. Emission Area     |                              | Fig.2             |

2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =20mA		2.0	2.4	V
Reverse Current	I <sub>r</sub>	V <sub>r</sub> =5V			10	uA
Brightness	I <sub>v</sub>	I <sub>f</sub> =20mA	50	90		mcd
Power Intensity	P <sub>o</sub>	I <sub>f</sub> =20mA	0.6	1.2		mW
Peak Wavelength	λ <sub>P</sub>	I <sub>f</sub> =20mA	605	615	625	nm
Spectral Radiation Bandwidth	Δλ	I <sub>f</sub> =20mA		20		nm
Rise Time	t <sub>r</sub>	I <sub>f</sub> =20mA		100		ns
Falltime	t <sub>f</sub>	I <sub>f</sub> =20mA		100		ns

‡ Die shall be mounted on TO=18 gold header without resin coated. (T<sub>a</sub>=25°C)

[Unit: um]

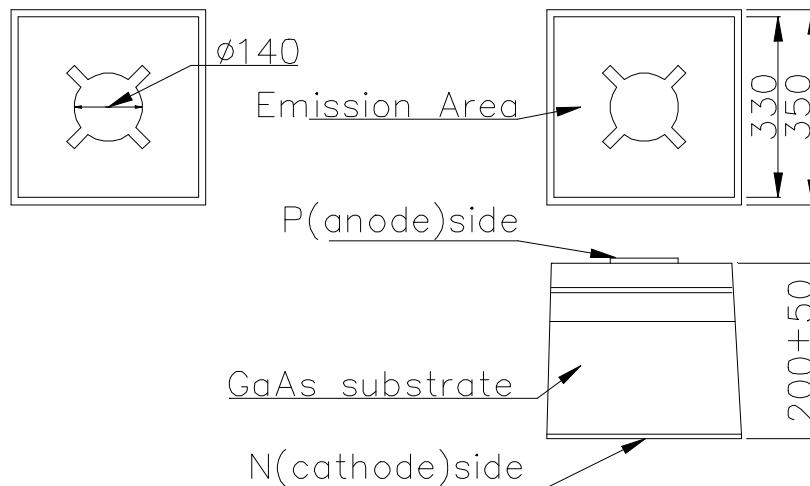


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area